



Package Style: Module, 10-Pin, 3mm x 3mm x 0.8mm

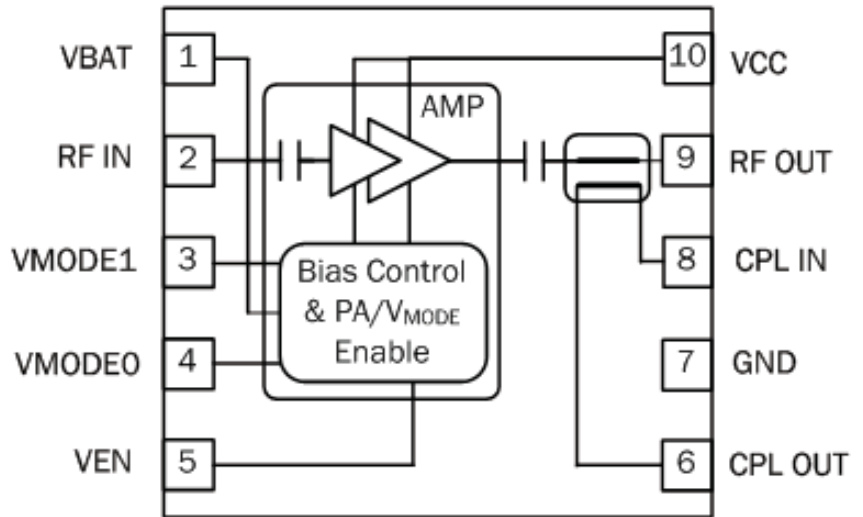


### Features

- Fully Compliant to LTE Modulation
- Best-in-Class Efficiency 44%, +28dBm Output Power
- High Power Gain: 32dB
- E-UTRA ACLR: -38dBc
- UTRA ACLR: -39dBc
- 5 MHz LTE Channel - Up to 25 Resource Blocks (RB)
- 10 MHz LTE Channel - Up to 50 Resource Blocks
- Optimized for DC-DC Converter Operation: RF6650 Recommended
- Three Power States with Digital Control Interface
- Integrated Power Coupler
- Integrated Blocking and Decoupling Capacitors

### Applications

- LTE Handsets
- LTE Datacards



Functional Block Diagram

### Product Description

The RF7317A is a high-power, high-efficiency linear power amplifier designed for use as final amplification stage in a 3V, 50Ω LTE mobile cellular equipment. This PA is developed for the E-UTRAN/LTE Band 17 operating in the 704MHz to 716MHz frequency range. The PA is specifically developed for up to 10MHz channel bandwidth on the Band 17 LTE network. The RF7317A has two digital control pins to select one of three power bias states to optimize performance and current drain at lower power levels. The part also has an integrated directional coupler which eliminates the need for an external discrete coupler at the output. The RF7317A is fully LTE compliant and is assembled in a 10-pin, 3mm x 3mm module.

### Ordering Information

RF7317A                      3V LTE Band 17 Linear PA Module  
 RF7317APCBA-410      Fully Assembled Evaluation Board

### Optimum Technology Matching® Applied

- |   |                                      |                                     |                                   |
|---|--------------------------------------|-------------------------------------|-----------------------------------|
| <input type="checkbox"/> GaAs HBT             | <input type="checkbox"/> SiGe BiCMOS | <input type="checkbox"/> GaAs pHEMT | <input type="checkbox"/> GaN HEMT |
| <input type="checkbox"/> GaAs MESFET          | <input type="checkbox"/> Si BiCMOS   | <input type="checkbox"/> Si CMOS    | <input type="checkbox"/> RF MEMS  |
| <input checked="" type="checkbox"/> InGaP HBT | <input type="checkbox"/> SiGe HBT    | <input type="checkbox"/> Si BJT     | <input type="checkbox"/> LDMS     |

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# RF7317A



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